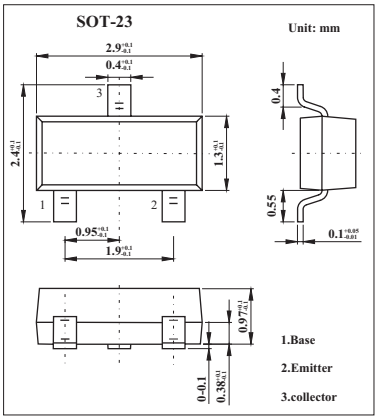
PNP Silicon Epitaxia

2SA1464



■ Features

● High fT: fT=400MHz.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-500	mA
Maximum Total power dissipation at 25℃ ambient temperature	P_T	200	mW
Maximum Junction temperature	T_j	150	℃
Maximum Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = -40V, I_E=0			-100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = -4V, I_C=0			-100	nA
DC current gain *	h_{FE}	V_{CE} = -2V , I_C = -150mA	75	140	300	
		V_{CE} = -2V , I_C = -500mA	20	50		
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = -500mA , I_B = -50mA		-0.45	-0.75	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C = -500mA , I_B = -50mA		-1	-1.3	V
Gain bandwidth product	f_T	V_{CE} = -10V , I_E = 20mA	150	400		MHz
Output capacitance	C_{ob}	V_{CB} = -10V , I_E = 0 , f = 1.0MHz		5	8	pF
Turn-on time	t_{on}	V_{CC} = -30V ,			35	ns
Storage time	t_{stg}	I_C = 150mA ,			225	ns
Turn-off time	t_{off}	I_{B1} = -I_{B2} = 15mA			255	ns

*. PW≤350μs,duty cycle≤2%

■ hFE Classification

Marking	Y12	Y13	Y14
hFE	75～150	100～200	150～300